

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
 (Not for submission under 37 CFR 1.99)

Application Number	10520647
Filing Date	2008-08-13
First Named Inventor	Marie D'Angelo
Art Unit	2822
Examiner Name	Chiu, TSZ K.
Attorney Docket Number	034299-617

U.S.PATENTS

Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
	1	7008886	B2	2006-03-07	Derycke et al.	

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U.S.PATENT APPLICATION PUBLICATIONS

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	1	20030102490	A1	2003-06-05	Kubo et al.	
	2	20040101625	A1	2004-05-27	Das et al.	
	3	20040104406	A1	2004-06-03	Derycke et al.	
	4	20050064639	A1	2005-03-24	Hisada et al.	

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FOREIGN PATENT DOCUMENTS

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	1	0703626	EP		1996-03-27			<input type="checkbox"/>
	2	2823770	EP		2002-10-25			<input type="checkbox"/>
	3	0139257	WO		2001-05-31			<input type="checkbox"/>
	4	02085778	WO		2002-10-31			<input type="checkbox"/>
	5	02086202	WO		2002-10-31			<input type="checkbox"/>
	6	2006005869	WO		2006-01-19			<input type="checkbox"/>
	7	2007003576	WO		2007-01-11			<input type="checkbox"/>
	8	2007003637	WO		2007-01-11			<input type="checkbox"/>
	9	2007003639	WO		2007-01-11			<input type="checkbox"/>

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	1	Amy, F. "Oxynitridation of Cubic Silicon Carbide (100) Surfaces," <i>J. Vac. Sci. Technol. A</i> . 17(5), Sep/Oct 1999, pp. 2629-2633.	<input type="checkbox"/>
	2	Aristov, V. Yu et al., "High Temperature Dismantling of Si Atomic Lines on β -SiC (100)," <i>Surface Science</i> 440, 1999, pp. L825-L830.	<input type="checkbox"/>
	3	Bandyopadhyay, S. et al., "Computational Paradigm for Nanoelectronics: Self-Assembled Quantum Dot Cellular Neural Networks," <i>IEE Procs-Circuits Devices Syst.</i> , Vol. 152, No. 2, April 2005, pp. 85-92.	<input type="checkbox"/>
	4	Derycke, V. et al., "Nanochemistry at the Atomic Scale Revealed in Hydrogen-Induced Semiconductor Surface Metalization," <i>Nature Materials</i> , Vol. 2, April 2003, pp. 253-258.	<input type="checkbox"/>
	5	Esaki, L. "New Phenomenon in Narrow Germanium p-n Junctions," <i>Letters to the Editor</i> , 2007, pp. 603-604.	<input type="checkbox"/>
	6	Ganem, J-J. et al., "NRA and XPS Characterizations of Layers Formed by Rapid Thermal Nitridation of Thin SiO ₂ films," <i>Nuclear Instruments and Methods in Physics Research B</i> 64 (1992), pp. 744-749.	<input type="checkbox"/>
	7	Haraguchi, K. et al., "GaAs p-n Junction Formed in Quantum Wire Crystals," <i>Appl. Phys. Lett.</i> 60 (6), February 1992, pp. 745-747.	<input type="checkbox"/>
	8	International Preliminary Examination Search Report, PCT/FR2005/050469, 2 pgs. February 11, 2005.	<input type="checkbox"/>
	9	Lyo, In-Whan et al., "Negative Differential Resistance on the Atomic Scale: Implications for Atomic Scale Devices," September 1989, pp. 1369-1371.	<input type="checkbox"/>
	10	Semond, F. et al., "Direct SiO ₂ / β -SiC(100)3x2 Interface Formation from 25 °C to 500 °C," <i>Appl. Phys. Lett.</i> 68 (15), April 1996, pp. 2144-2146.	<input type="checkbox"/>
	11	Soukiasian, P. et al., "Highly Stable Si Atomic Line Formation on the β -SiC(100) Surface," <i>Physical Review Letters</i> , Volume 79, Number 13, September 1997, pp. 2498-2501.	<input type="checkbox"/>

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	12	Soukiasian P. et al. "Atomic Scale Control and Understanding of Cubic Silicon Carbide Surface Reconstructions, Nanostructures and Nanochemistry" Journal of Physics: Condensed Matter IOP Publishing UK, Vol. 16, No. 17, May 2004, pp. S1611-S1658.	<input type="checkbox"/>
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